

# DATA SHEET



## **BC556; BC557** PNP general purpose transistors

Product data sheet  
Supersedes data of 1999 Apr 15

2004 Oct 11

# PNP general purpose transistors

# BC556; BC557

### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

### APPLICATIONS

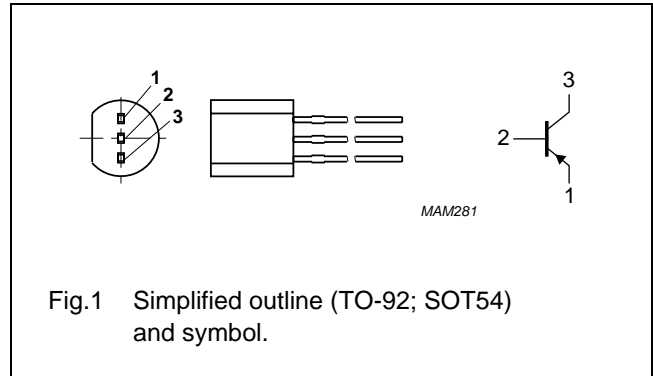
- General purpose switching and amplification.

### DESCRIPTION

PNP transistor in a TO-92; SOT54 plastic package.  
NPN complements: BC546 and BC547.

### PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector



### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BC556	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BC557			

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter			
	BC556		–	–80	V
	BC557		–	–50	V
$V_{CEO}$	collector-emitter voltage	open base			
	BC556		–	–65	V
	BC557		–	–45	V
$V_{EBO}$	emitter-base voltage	open collector	–	–5	V
$I_C$	collector current (DC)		–	–100	mA
$I_{CM}$	peak collector current		–	–200	mA
$I_{BM}$	peak base current		–	–200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	500	mW
$T_{stg}$	storage temperature		–65	+150	$^\circ\text{C}$
$T_j$	junction temperature		–	150	$^\circ\text{C}$
$T_{amb}$	ambient temperature		–65	+150	$^\circ\text{C}$

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	250	K/W

## Note

1. Transistor mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

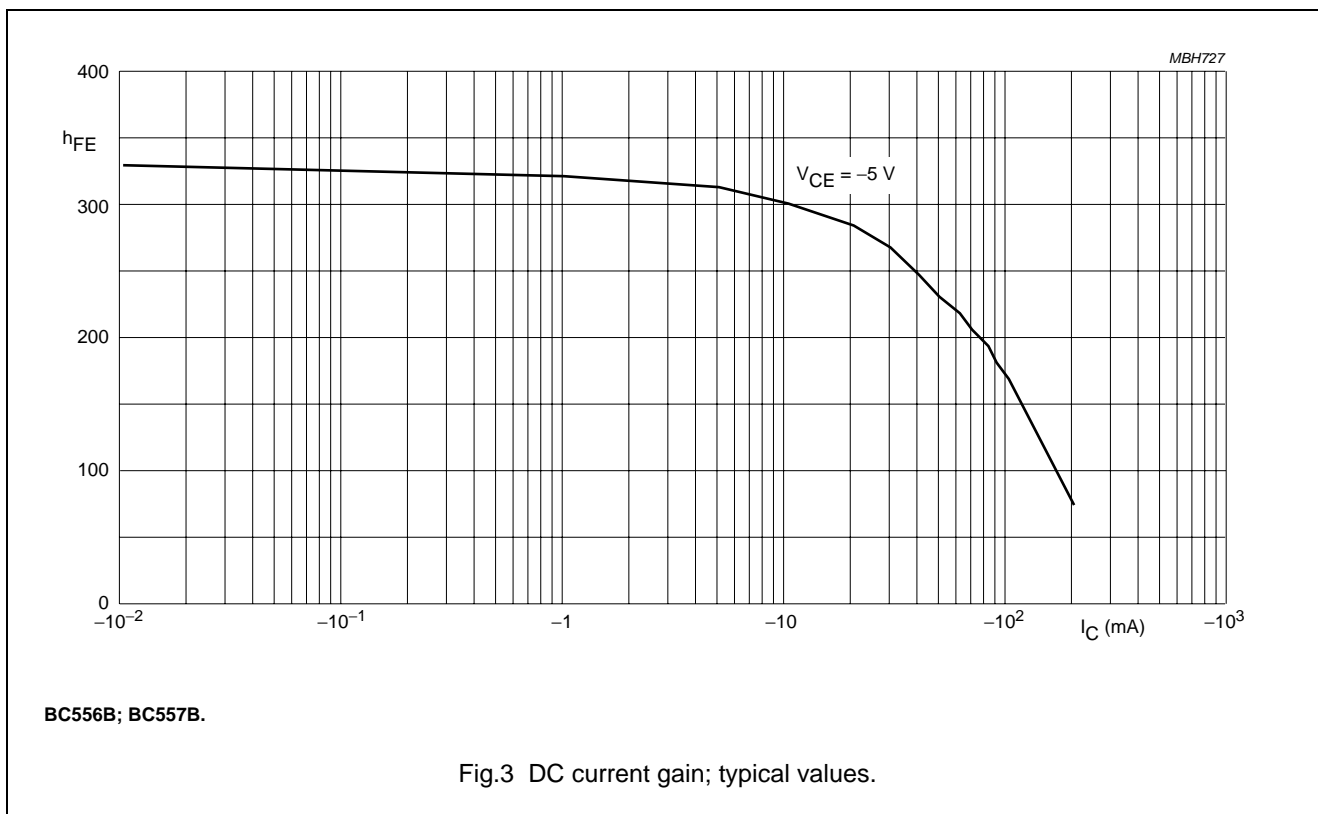
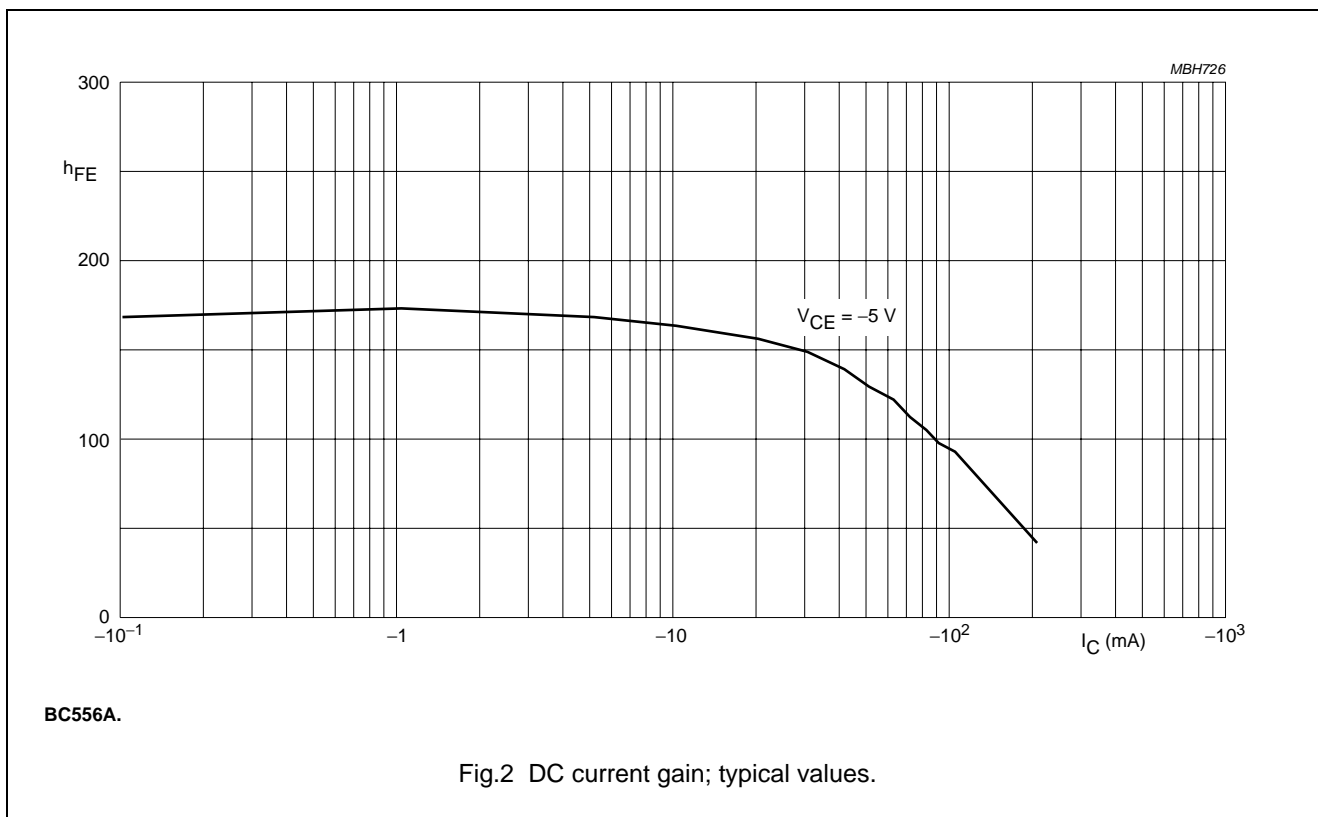
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -30\text{ V}; I_E = 0\text{ A}$	–	–1	–15	nA
		$V_{CB} = -30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ °C}$	–	–	–4	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ V}$	–	–	–100	nA
$h_{FE}$	DC current gain BC556 BC557 BC556A BC556B; BC557B BC557C	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V};$ see Figs 2, 3 and 4	125	–	475	
			125	–	800	
			125	–	250	
			220	–	475	
			420	–	800	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–60	–300	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA}$	–	–180	–650	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA};$ note 1	–	–750	–	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA};$ note 1	–	–930	–	mV
$V_{BE}$	base-emitter voltage	$V_{CE} = -5\text{ V}; I_C = -2\text{ mA};$ note 2	–600	–650	–750	mV
		$V_{CE} = -5\text{ V}; I_C = -10\text{ mA};$ note 2	–	–	–820	mV
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	–	3	–	pF
$C_e$	emitter capacitance	$V_{EB} = -0.5\text{ V}; I_C = i_c = 0\text{ A}; f = 1\text{ MHz}$	–	10	–	pF
$f_T$	transition frequency	$V_{CE} = -5\text{ V}; I_C = -10\text{ mA}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$V_{CE} = -5\text{ V}; I_C = -200\text{ }\mu\text{A}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	2	10	dB

## Notes

1.  $V_{BEsat}$  decreases by about  $-1.7\text{ mV/K}$  with increasing temperature.
2.  $V_{BE}$  decreases by about  $-2\text{ mV/K}$  with increasing temperature.

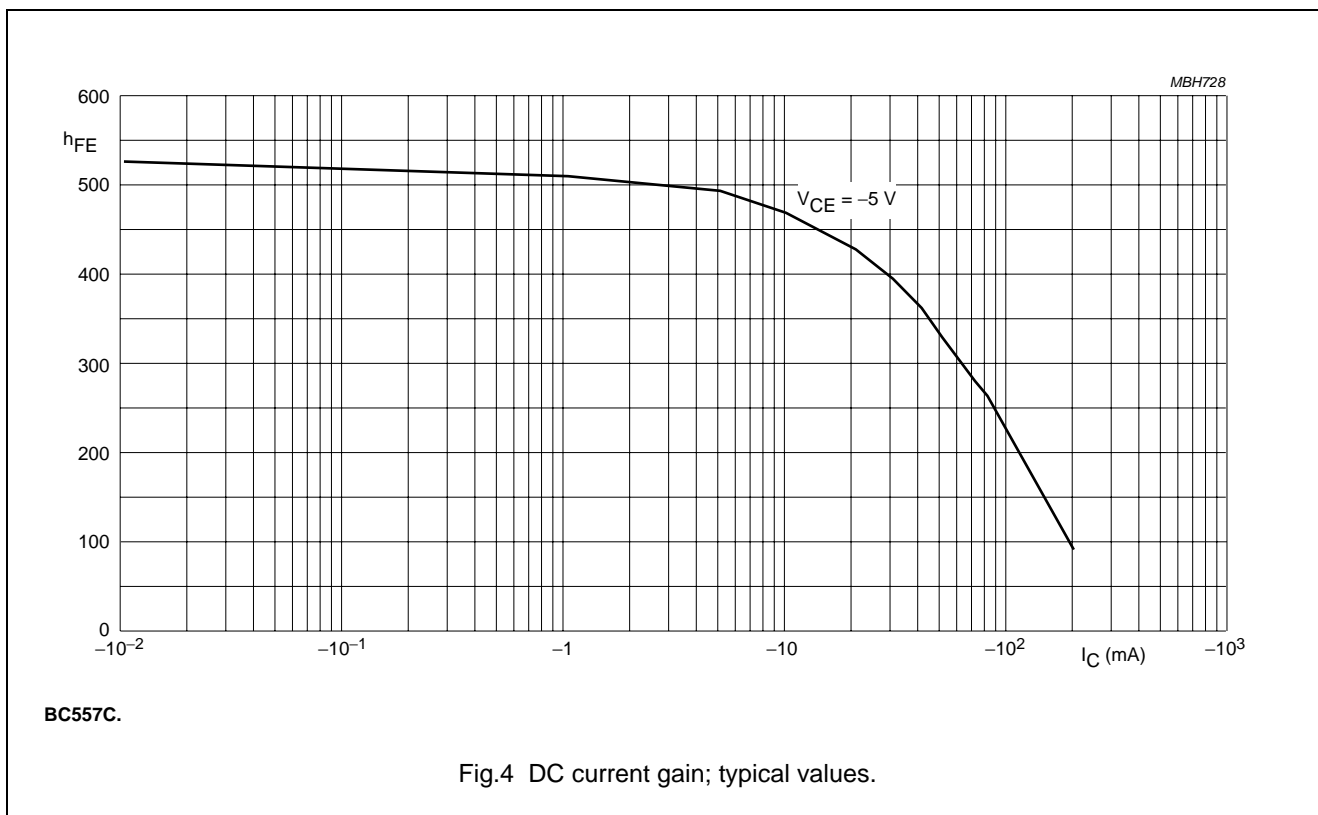
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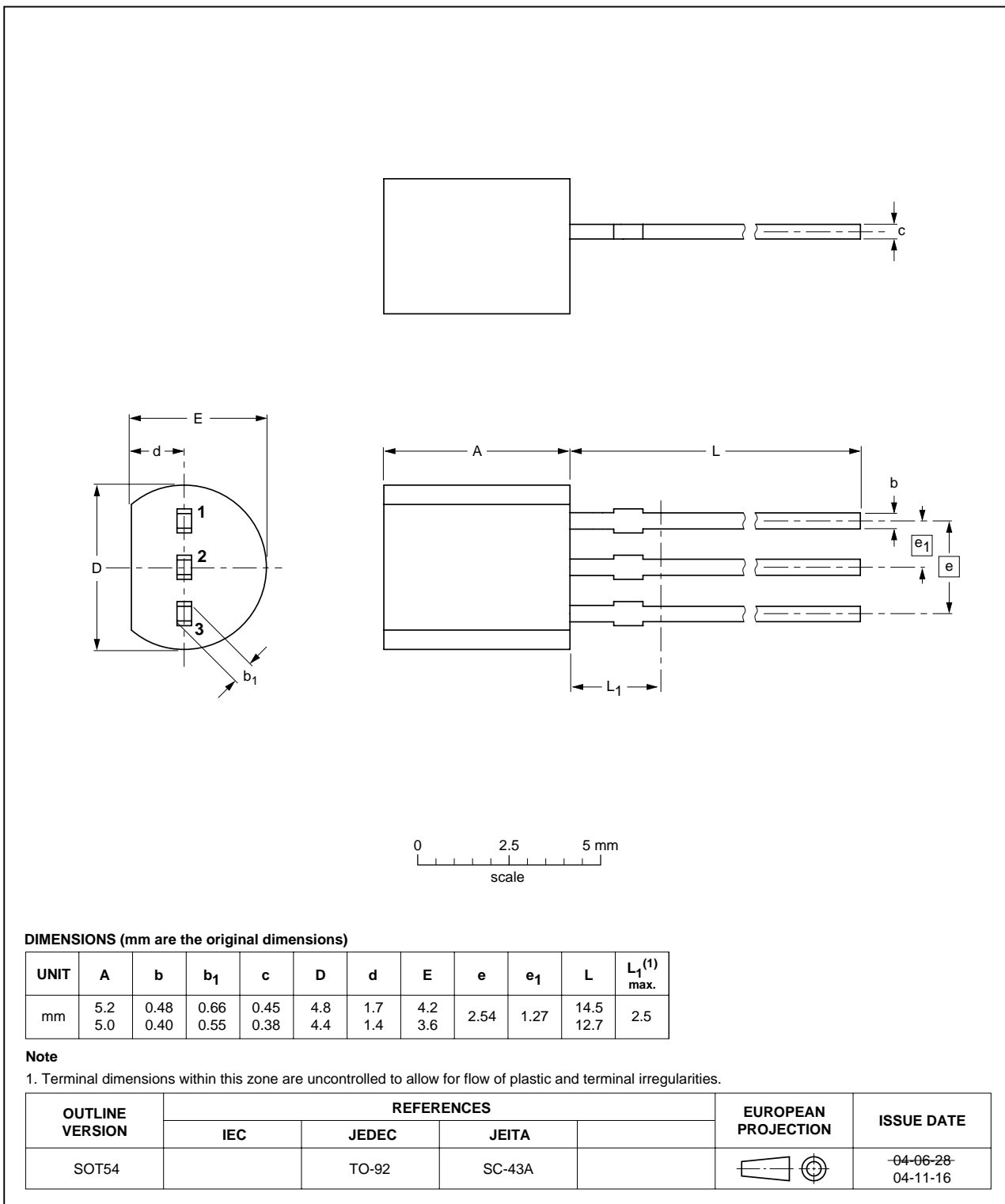
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



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## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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# ***NXP Semiconductors***

## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

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